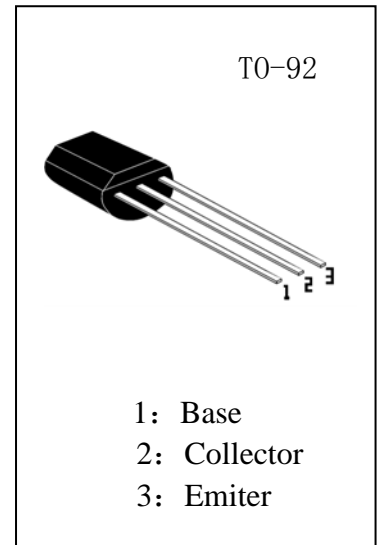


低压低噪晶体管

- 集电极电流 $I_c = -100\text{mA}$
- 耗散功率 $P_c = 450\text{mW}$
- 与 S9014 对管

极限参数(Absolute Maximum Ratings) $T_a = 25^\circ\text{C}$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	-50	V
Collector-Emitter Voltage	V_{ceo}	-45	V
Emitter-Base Voltage	V_{ebo}	-5	V
Collector Current	I_c	-100	mA
Collector Dissipation	P_c	450	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~150	$^\circ\text{C}$



电性能(Electrical Characteristic) $T_a = 25^\circ\text{C}$

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
BV_{cbo}	Collector-Base Breakdown Voltage	$I_c = -100\mu\text{A}$ $I_e = 0$	-50			V
BV_{ceo}	Collector-Emitter Breakdown Voltage	$I_c = -1\text{mA}$ $I_b = 0$	-45			V
BV_{ebo}	Emitter-Base Breakdown Voltage	$I_e = -100\mu\text{A}$ $I_c = 0$	-5			V
I_{cbo}	Collector Cutoff Current	$V_{cb} = -50\text{V}$, $I_e = 0$			-50	nA
I_{ebo}	Emitter Cutoff Current	$V_{eb} = -5\text{V}$, $I_c = 0$			-50	nA
I_{ceo}	Collector Cutoff Current	$V_{ce} = -40\text{V}$, $I_b = 0$			-1	μA
$V_{ce(sat)}$	Collector-Emitter Saturation Voltage	$I_c = -100\text{mA}$, $I_b = -5\text{mA}$		-0.2	-0.7	V
$V_{be(sat)}$	Base-Emitter Saturation Voltage	$I_c = -100\text{mA}$, $I_b = -5\text{mA}$		-0.87	-1.0	V
$V_{be(on)}$	Base-Emitter On Voltage	$V_{ce} = -5\text{V}$, $I_c = -2\text{mA}$	-0.6	-0.65	-0.75	V
H_{fe}	DC Current Gain	$V_{ce} = -5\text{V}$, $I_c = -1\text{mA}$	60		1000	
C_{ob}	Output Capacitance	$V_{cb} = -10\text{V}$, $I_e = 0$, $f = 1\text{MHz}$		4.5	7	PF
f_T	Current Gain-Bandwidth product	$V_{ce} = -5\text{V}$, $I_c = -10\text{mA}$	100	190		MHz
NF	Noise Figure	$V_{ce} = -5\text{V}$, $I_c = -0.2\text{mA}$ $f = 1\text{KHz}$, $R_s = 2\text{K}\Omega$		0.7	10	dB

Class	A		B		C		
	60-100	100-200	200-300	300-400	400-500	500-600	600-1000
H_{fe}	60-100	100-200	200-300	300-400	400-500	500-600	600-1000